

HD74CBT1G125

Single FET Bus Switch

REJ03D0815-0100

(Previous: ADE-205-645)

Rev.1.00 Apr 07, 2006

Description

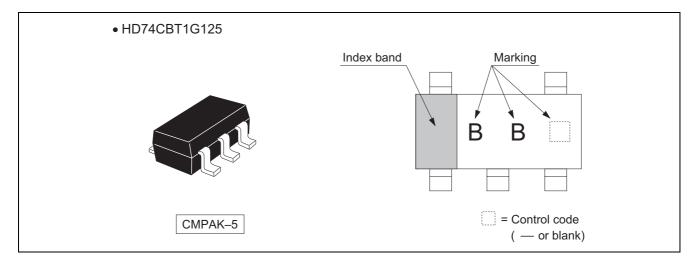
The HD74CBT1G125 features a single high-speed line switch. The switch is disabled when the output enable (\overline{OE}) input is high.

Features

- Minimal propagation delay through the switch.
- 5Ω switch connection between two ports.
- TTL-compatible input levels.
- Ultra low quiescent power.
 - Ideally suited for notebook applications.
- Ordering Information

Part Name	Package Type	Package Code (Previous code)	Package Abbreviation	Taping Abbreviation (Quantity)
HD74CBT1G125CME	'	PTSP0005ZC-A (CMPAK-5V)	СМ	E (3,000pcs / Reel)

Outline and Article Indication

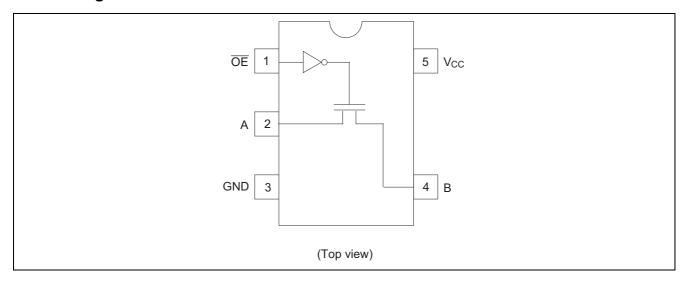


Function Table

Input OE	Function
L	A port = B port
Н	Disconnect

H: High level L: Low level

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage range	V _{CC}	-0.5 to 7.0	V	
Input voltage range *1	Vı	-0.5 to 7.0	V	
Input clamp current	I _{IK}	-50	mA	V _I < 0
Continuous output current	Io	128	mA	$V_0 = 0$ to V_{CC}
Continuous current through V _{CC} or GND	I _{CC} or I _{GND}	±100	mA	
Maximum power dissipation at Ta = 25 °C (in still air) *2	P _T	200	mW	
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

- 1. The input and output voltage ratings may be exceeded even if the input and output clamp-current ratings are observed.
- 2. The maximum package power dissipation was calculated using a junction temperature of 150°C.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V _{CC}	4.0	5.5	V	
Input voltage range	VI	0	5.5	V	
Output voltage range	V _{I/O}	0	5.5	V	
Input transition rise or fall rate	Δt / Δν	0	5	ns / V	V _{CC} = 4.5 to 5.5 V
Operating free-air temperature	Та	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

DC Electrical Characteristics

 $(Ta = -40 \text{ to } 85^{\circ}C)$

Item	Symbol	V _{CC} (V)	Min	Typ *1	Max	Unit	Test conditions
Clamp diode voltage	V _{IK}	4.5	_	_	-1.2	V	$I_{IN} = -18 \text{ mA}$
Input voltage	V _{IH}	4.0 to 5.5	2.0	_	_	V	
	V _{IL}	4.0 to 5.5	_	_	0.8		
On-state switch resistance *2	Ron	4.0	_	14	20	Ω	$V_{IN} = 2.4 \text{ V}, I_{IN} = 15 \text{ mA}$ Typ at $V_{CC} = 4.0 \text{ V}$
		4.5		5	7		V _{IN} = 0 V, I _{IN} = 64 mA
		4.5	_	5	7		V _{IN} = 0 V, I _{IN} = 30 mA
		4.5		10	15		$V_{IN} = 2.4 \text{ V}, I_{IN} = 15 \text{ mA}$
Input current	I _{IN}	0 to 5.5		_	±1.0	μΑ	$V_{IN} = 5.5 \text{ V or GND}$
Off-state leakage current	loz	5.5		_	±1.0	μΑ	$0 \le A, B \le V_{CC}$
Quiescent supply current	Icc	5.5	_	_	1.0	μΑ	$V_{IN} = V_{CC}$ or GND, $I_O = 0$ mA
Increase in I _{CC} per input *3	Δlcc	5.5	_	_	2.5	mA	One input at 3.4 V, other inputs at V _{CC} or GND

Notes: For condition shown as Min or Max use the appropriate values under recommended operating conditions.

- 1. All typical values are at $V_{CC} = 5 \text{ V}$ (unless otherwise noted), $Ta = 25^{\circ}C$.
- 2. Measured by the voltage drop between the A and B terminals at the indicated current through the switch. On-state resistance is determined by the lower voltage of the two (A or B) terminals.
- 3. This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

Capacitance

 $(Ta = 25^{\circ}C)$

Item	Symbol	V _{cc} (V)	Min	Тур	Max	Unit	Test conditions
Control input capacitance	C _{IN}	5.0	_	3	_	pF	V _{IN} = 0 or 3 V
Input / output capacitance	C _{I/O (OFF)}	5.0	_	5	_	pF	$V_O = 0$ or 3 V, $\overline{OE} = V_{CC}$

Note: This parameter is determined by device characterization is not production tested.

Switching Characteristics

 $(Ta = -40 \text{ to } 85^{\circ}C)$

 $V_{CC} = 4.0 \text{ V}$

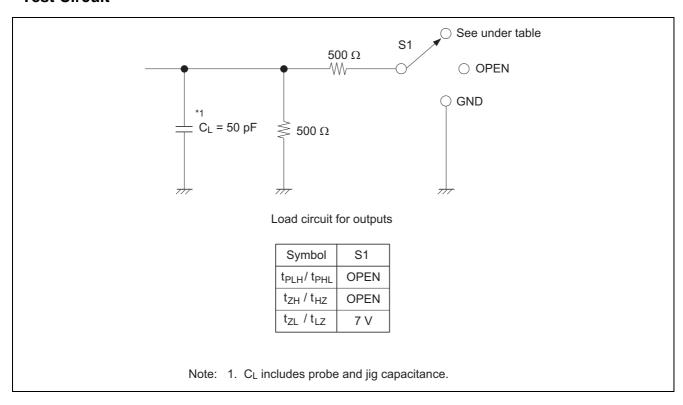
Item	Symbol	Min	Max	Unit	Test conditions	FROM (Input)	TO (Output)
Propagation delay time *1	t _{PLH}	_	0.35	ns	$C_L = 50 \text{ pF}$	A or B	B or A
	t _{PHL}				$R_L = 500 \Omega$		
Enable time	t _{ZH}	_	5.5	ns	$C_L = 50 \text{ pF}$	OE	A or B
	t_{ZL}				$R_L = 500 \Omega$		
Disable time	t _{HZ}	_	4.5	ns	C _L = 50 pF	OE	A or B
	t _{LZ}	_	4.5		$R_L = 500 \Omega$		

 $V_{CC} = 5.0 \pm 0.5 \text{ V}$

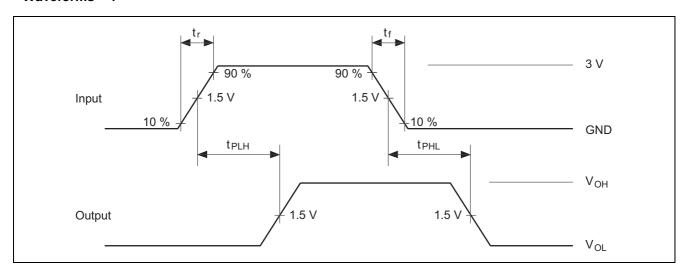
Item	Symbol	Min	Max	Unit	Test conditions	FROM (Input)	TO (Output)
Propagation delay time *1	t _{PLH}	_	0.25	ns	$C_L = 50 \text{ pF}$	A or B	B or A
	t _{PHL}				$R_L = 500 \Omega$		
Enable time	t _{ZH}	1.6	4.9	ns	$C_L = 50 \text{ pF}$	OE	A or B
	t_{ZL}				$R_L = 500 \Omega$		
Disable time	t _{HZ}	1.0	4.2	ns	C _L = 50 pF	OE	A or B
	t _{LZ}	1.0	4.8		$R_L = 500 \Omega$		

Note: 1. The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

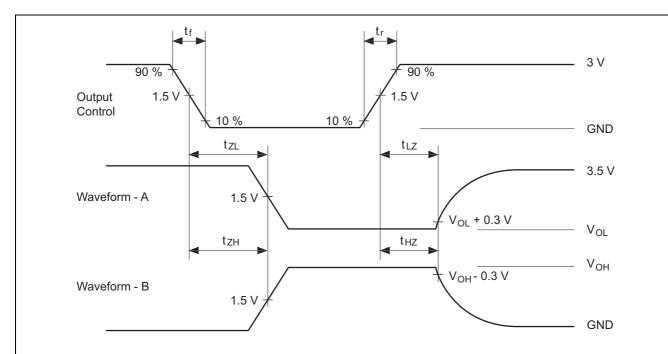
Test Circuit



Waveforms - 1



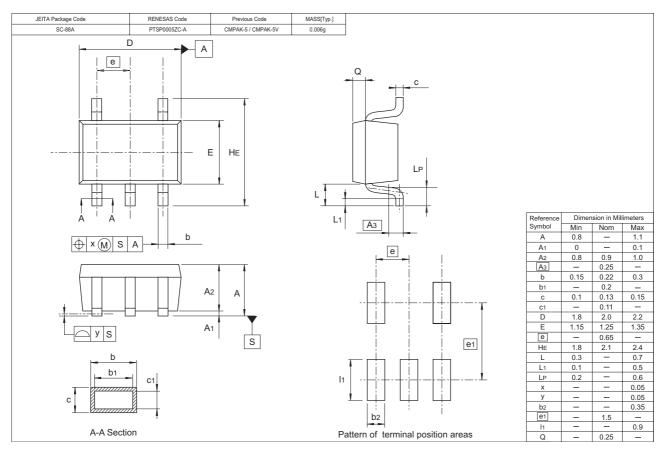
Waveforms - 2



Notes: 1. All input pulses are supplied by generators having the following characteristics : PRR \leq 10 MHz, Z_O = 50 Ω , $t_r \leq$ 2.5 ns, $t_f \leq$ 2.5 ns.

- 2. Waveform A is for an output with internal conditions such that the output is low except when disabled by the output control.
- 3. Waveform B is for an output with internal conditions such that the output is high except when disabled by the output control.
- 4. The output are measured one at a time with one transition per measurement.

Package Dimensions



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